

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-16V	19mΩ@-4.5V	-6A
	27mΩ@-2.5V	



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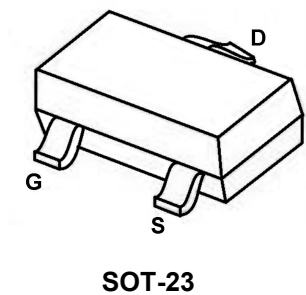
Feature

- High power and current handling capability
- Surface mount package

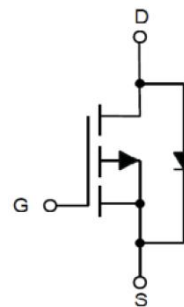
Application

- Battery Switch
- DC/DC Converter

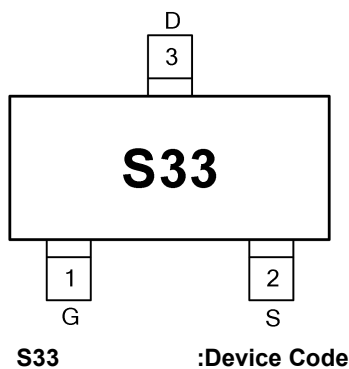
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
SP2333T2	SOT-23	3000

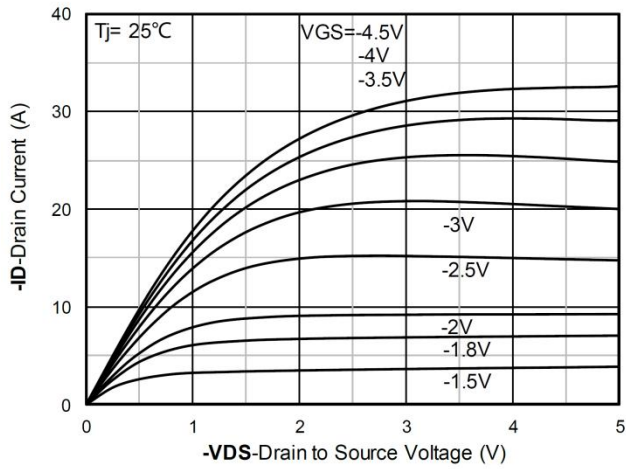
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-6	A
Pulse Drain Current Tested	I_{DM}	-24	A
Power Dissipation	P_D	1.8	W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	69	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

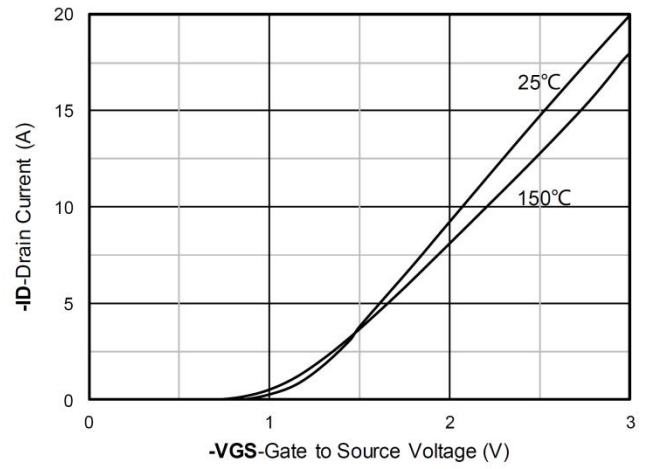
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=-250μA	-16	-	-	V
Drain-Source Leakage Current	IDSS	VDS=-13V , VGS=0V	-	-	-1	uA
Gate-Source Leakage Current	IGSS	VGS=±8V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=-250μA	-0.4	-0.65	-1.0	V
Static Drain-Source On-Resistance	RDS(on)	VGS=-4.5V , ID=-5A	-	19	28	mΩ
		VGS=-2.5V , ID=-4.3A	-	27	40	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=-6V , VGS=0V , f=1MHz	-	1275	-	pF
Output Capacitance	Coss		-	255	-	
Reverse Transfer Capacitance	Crss		-	236	-	
Total Gate Charge	Qg	VDS=-6V , VGS=-4.5V , ID=-5A	-	14	-	nC
Gate-Source Charge	Qgs		-	2.3	-	
Gate-Drain Charge	Qgd		-	3.6	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=-6V VGS=-4.5V , RG=1Ω, ID=-4A	-	26	-	nS
Turn-On Rise Time	tr		-	24	-	
Turn-Off Delay Time	td(off)		-	45	-	
Turn-Off Fall Time	tf		-	20	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=-1A , TJ=25℃	-	-	-1.2	V

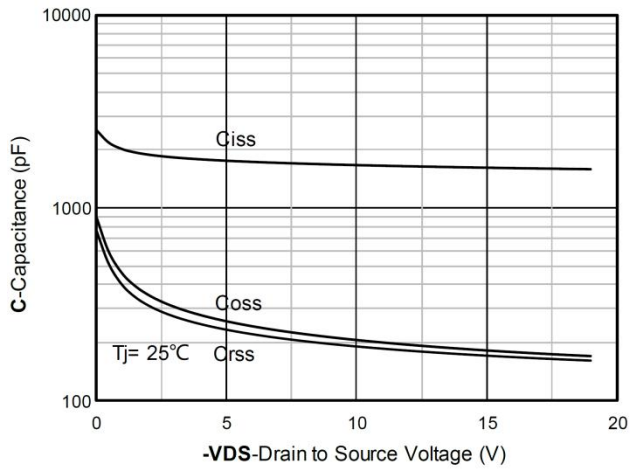
Typical Characteristics



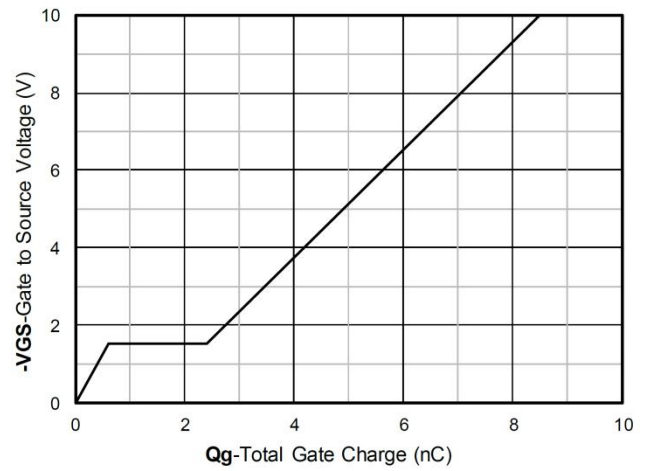
Output Characteristics



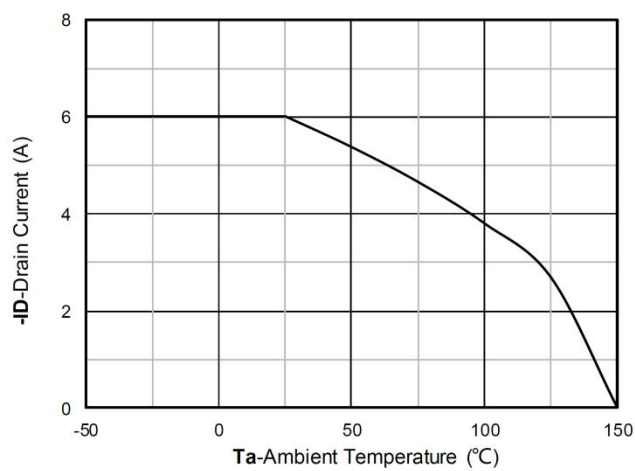
Transfer Characteristics



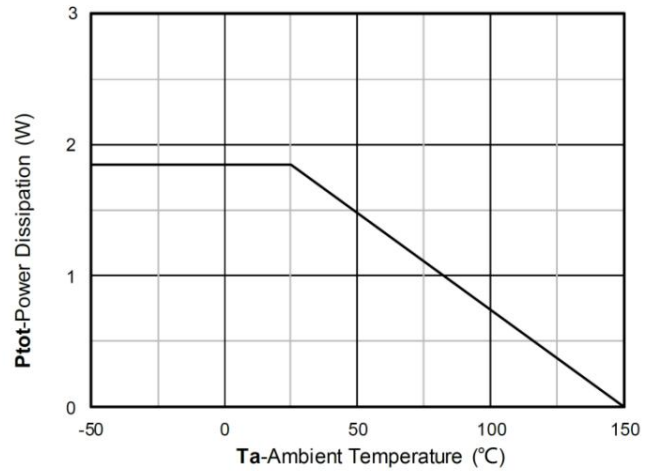
Capacitance Characteristics



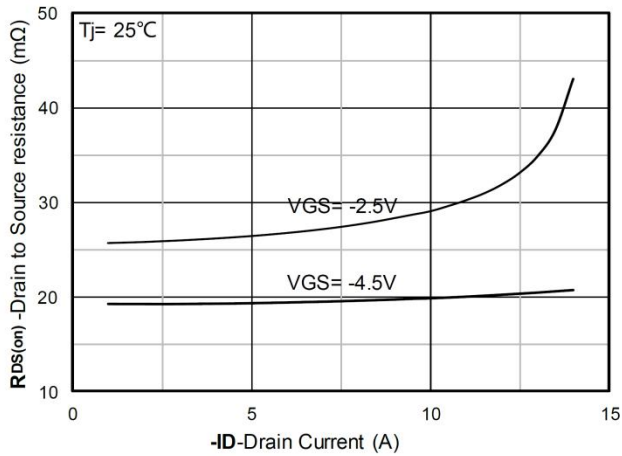
Gate Charge



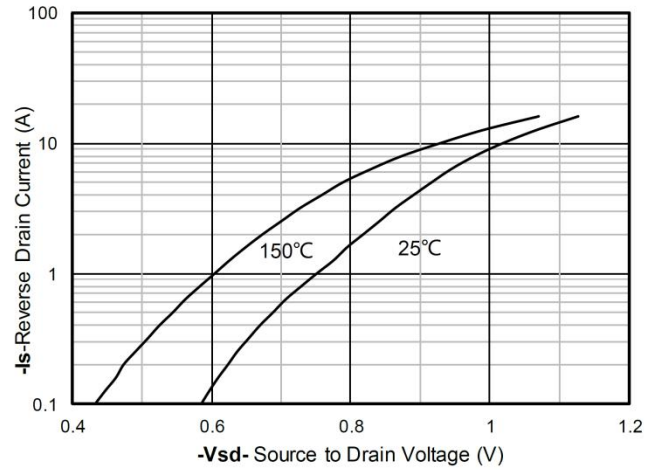
Current dissipation



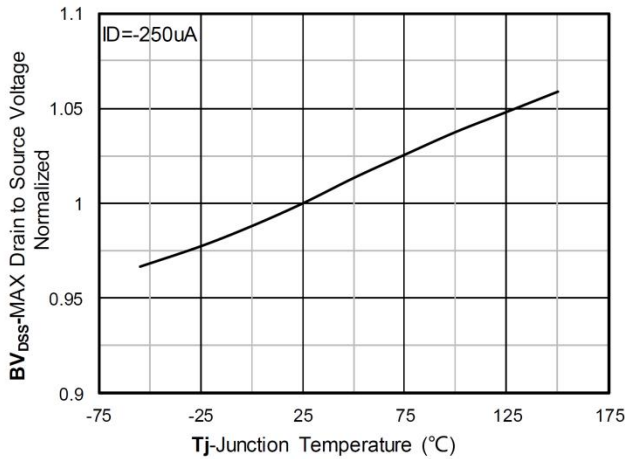
Power dissipation



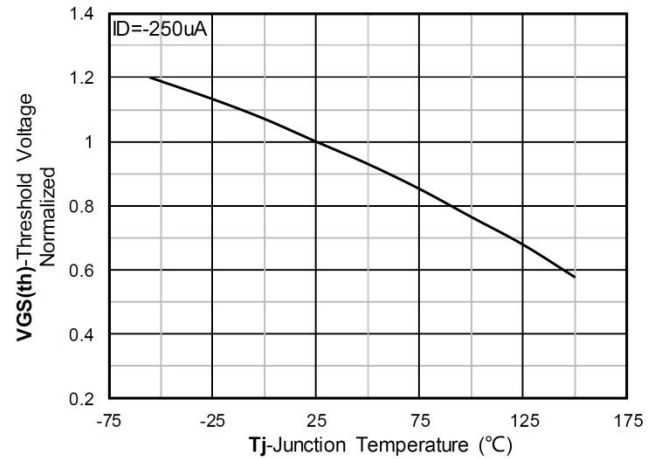
$R_{DS(on)}$ VS Drain Current



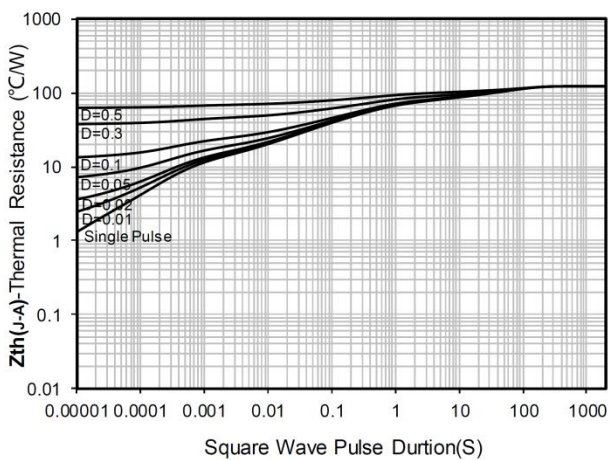
Forward characteristics of reverse diode



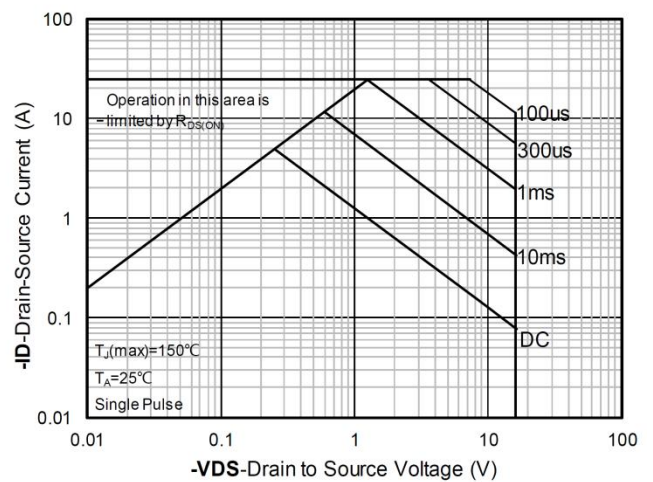
Normalized breakdown voltage



Normalized Threshold voltage

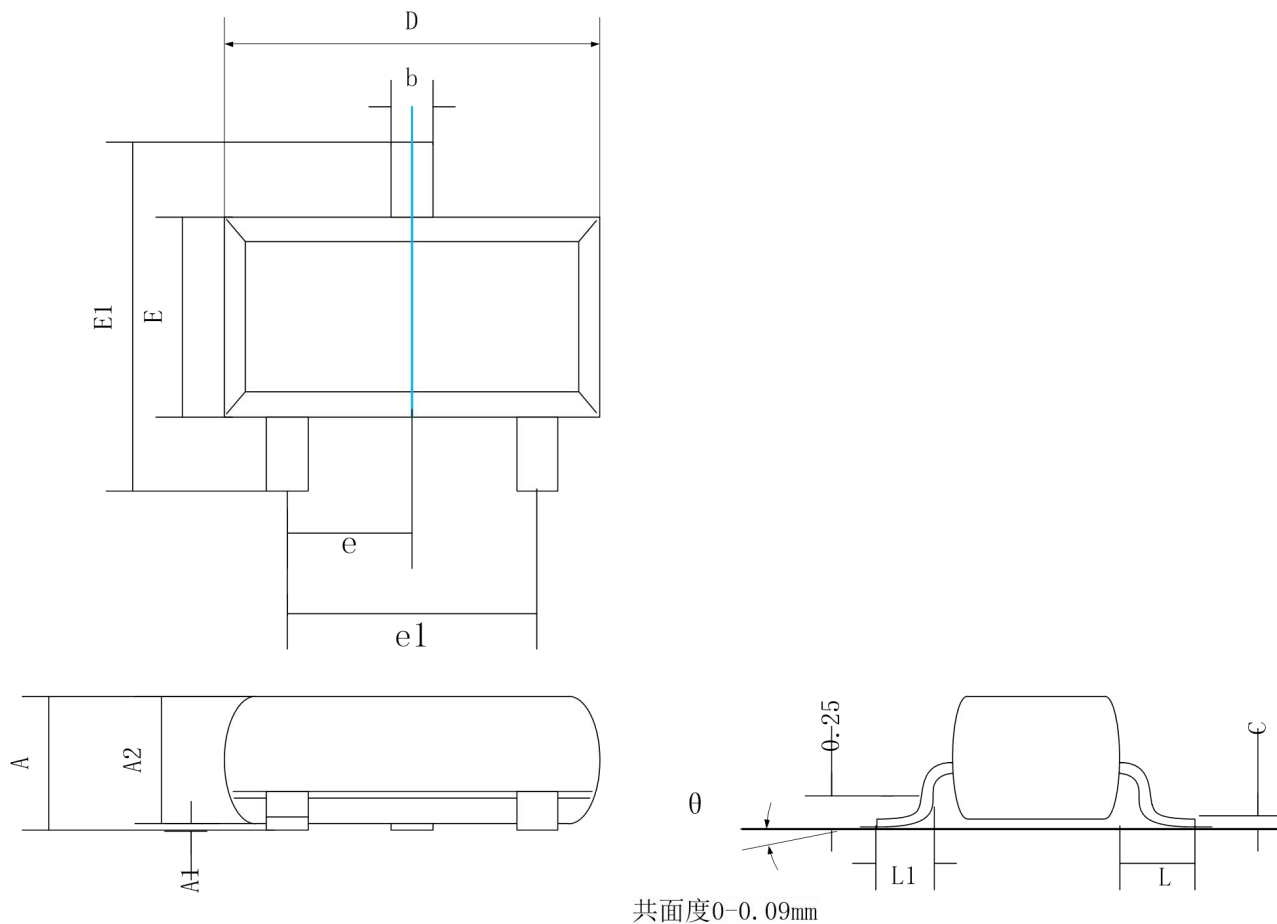


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°

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